

20V N-Channel Enhancement Mode MOSFET

Description

The PECN2012DR uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

- ◆ $V_{DS} = 20V$, $I_D = 12A$
 $R_{DS(ON)}(Typ.) = 15m\Omega$ @ $V_{GS} = 2.5V$
 $R_{DS(ON)}(Typ.) = 12m\Omega$ @ $V_{GS} = 4.5V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

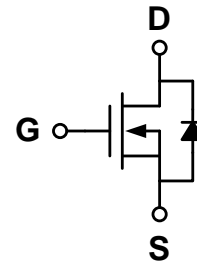
Application

- ◆ PWM applications
- ◆ Load switch

Package

- ◆ DFN2*2-6L-B

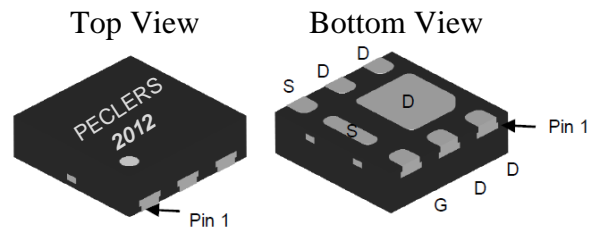
Schematic diagram



Marking and pin assignment

DFN2*2-6L-B

(Thickness 0.55mm)



2012----PECLERS 2012



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PECN2012DR	-55°C to +150°C	DFN2*2-6L-B	4000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V_{GS}	±12	V
Drain current-continuous ^a @Tj=125°C -pulse ^b	I_D	12	A
	I_{DM}	48	A
Drain-source Diode forward current	I_S	12	A
Maximum power dissipation	P_D	18	W
Operating junction Temperature range	T_j	-55—150	°C

